Yueheng Zhang

List of Publications by Year in descending order

27 papers	289 citations	840776 11 h-index	940533 16 g-index
27 all docs	27 docs citations	27 times ranked	261 citing authors

#	Article	IF	Citations
1	InAs/GaAs p-type quantum dot infrared photodetector with higher efficiency. Applied Physics Letters, 2013, 103, .	3.3	43
2	Broadband THz to NIR up-converter for photon-type THz imaging. Nature Communications, 2019, 10, 3513.	12.8	28
3	Noise, gain, and capture probability of p-type InAs-GaAs quantum-dot and quantum dot-in-well infrared photodetectors. Journal of Applied Physics, 2017, 121, 244501.	2.5	22
4	Tunable Cherenkov Radiation of Phonon Polaritons in Silver Nanowire/Hexagonal Boron Nitride Heterostructures. Nano Letters, 2020, 20, 2770-2777.	9.1	19
5	Terahertz quantum-well photodetectors: Design, performance, and improvements. Journal of Applied Physics, 2013, 114, 194507.	2.5	15
6	Study on the quantum efficiency of resonant cavity enhanced GaAs far-infrared detectors. Journal of Applied Physics, 2002, 91, 5538-5544.	2.5	14
7	Infrared single photon detector based on optical up-converter at 1550â€‰nm. Scientific Reports, 2017, 7, 15341.	3.3	14
8	Temperature dependence of Raman scattering in GaMnN. Applied Physics Letters, 2006, 89, 161920.	3.3	13
9	Realization of the high-performance THz GaAs homojunction detector below the frequency of Reststrahlen band. Applied Physics Letters, 2018, 113, .	3.3	13
10	Demonstration of bottom mirrors for resonant-cavity-enhanced GaAs homojunction far-infrared detectors. Applied Physics Letters, 2003, 82, 1129-1131.	3.3	12
11	High-Temperature Photon-Noise-Limited Performance Terahertz Quantum-Well Photodetectors. IEEE Transactions on Terahertz Science and Technology, 2015, 5, 715-724.	3.1	12
12	Temperature dependence of the optical properties in GaMnN. Journal of Applied Physics, 2006, 99, 113533.	2.5	11
13	Study of valence-band intersublevel transitions in InAs/GaAs quantum dots-in-well infrared photodetectors. Applied Physics Letters, 2014, 104, .	3.3	11
14	Broadband and photovoltaic THz/IR response in the GaAs-based ratchet photodetector. Science Advances, 2022, 8, .	10.3	11
15	High temperature terahertz response in a p-type quantum dot-in-well photodetector. Applied Physics Letters, 2014, 105, 151107.	3.3	10
16	Dark current mechanism of terahertz quantum-well photodetectors. Journal of Applied Physics, 2014, 116, .	2.5	8
17	Cryogenic characteristics of GaAs-based near-infrared light emitting diodes. Semiconductor Science and Technology, 2020, 35, 035021.	2.0	7
18	Ultra-broadband THz/IR upconversion and photovoltaic response in semiconductor ratchet-based upconverter. Applied Physics Letters, 2021, 119, .	3.3	6

#	Article	IF	Citations
19	Optical field simulation of edge coupled terahertz quantum well photodetectors. AIP Advances, 2018, 8, 035214.	1.3	5
20	Optical coupling enhancement of multi-color terahertz quantum well detector. Journal of Applied Physics, 2021, 130, 203102.	2.5	5
21	Performance optimization of resonant cavity enhanced n-GaAs homojunction far-infrared detectors: A theoretical study. Journal of Applied Physics, 2009, 105, 084515.	2.5	3
22	Optimization of the Cryogenic Light-Emitting Diodes for High-Performance Broadband Terahertz Upconversion Imaging. Frontiers in Physics, 2021, 9, .	2.1	3
23	Quantum well infrared photodetector simultaneously working inÂtwo atmospheric windows. Applied Physics A: Materials Science and Processing, 2010, 100, 415-419.	2.3	2
24	Highâ€Efficiency Interdigitated Back Contact Silicon Solar Cells with Front Floating Emitter. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900445.	1.8	2
25	Response to â€œComment on â€˜Study on the quantum efficiency of resonant cavity enhanced GaAs far-infrared detectorsâ€â€™ [J. Appl. Phys.93, 786 (2003)]. Journal of Applied Physics, 2003, 93, 788-788.	2.5	0
26	Performance of terahertz quantum-well photodetectors. , 2015, , .		0
27	Quantum ratchet broadband THz detector. , 2021, , .		0